



NPN Saturated Switches

Device No.	Case Style	V <sub>CE</sub> * V <sub>CB0</sub> (V) Min	V <sub>CEO</sub> (V) Min	V <sub>EBO</sub> (V) Min	I <sub>CB0</sub> (mA) Max	V <sub>CB</sub> (V) @ I <sub>C</sub>	h <sub>FE</sub> @ I <sub>C</sub> & V <sub>CE</sub> (V)	V <sub>CE(SAT)</sub> (V) Max	V <sub>BE(SAT)</sub> (V) Max	I <sub>C</sub> (mA) @ I <sub>C</sub> = 10	C <sub>ob</sub> (pF) Max	f <sub>T</sub> (MHz) Min	I <sub>C</sub> (mA)	t <sub>(on)</sub> (ns) Max	Test Conditions	Process No.
2N5769	TO-92 (92)	40	15	4.5	400	20	100 1 30 0.4 40 120 10 0.35	0.2 0.25 0.5	0.7 1.5 1.6	10 30 100	4	500	10	18	(Note 1)	21
PN2369	TO-92 (92)	40	15	4.5	400	20	100 2 40 120 10 1	0.25	0.7	10	4	500	10	18	(Note 1)	21
PN2369A	TO-92 (92)	40	15	4.5	400	20	100 1 30 0.4 40 120 10 1 40 10 0.35	0.2 0.2 0.5	0.7 1.15 1.6	10 30 100	4	500	10	18	(Note 1)	21 (5-24)
PN4275	TO-92 (92)	40*	15	4.5	500	20	100 1 30 0.4 35 120 10 1	0.2 0.25 0.5	0.72 1.15 1.6	10 30 100	4	400	10	12	(Note 2)	21
PN5134	TO-92 (92)	20*	10	3.5	100	15	30 0.4 20 150 10 1	0.25	0.7	10	4	250	10	18	(Note 2)	21
TN3725A	TO-226 (99)	60	50	6	1.7	60	1A 5 800 2 35 500 1 40 300 1 60 150 100 1 30 10 1	0.25 0.26 0.4 0.25 0.8 0.95	0.76 0.86 1.1 0.9 1.5 1.7	10 100 300 500 800 1A	10	300	50	60	(Note 4)	25 (5-59)

Note 1: V<sub>CC</sub> = 3V, I<sub>C</sub> = 10 mA, I<sub>B</sub><sup>1</sup> = 3 mA, I<sub>B</sub><sup>2</sup> = 1.5 mA.

Note 2: V<sub>CC</sub> = 3V, I<sub>C</sub> = 10 mA, I<sub>B</sub><sup>1</sup> = I<sub>B</sub><sup>2</sup> = 3.3 mA.

Note 3: V<sub>CC</sub> = 10V, I<sub>C</sub> = 300 mA, I<sub>B</sub><sup>1</sup> = I<sub>B</sub><sup>2</sup> = 30 mA.

TEST CONDITIONS

Note 4: V<sub>CC</sub> = 30V, I<sub>C</sub> = 500 mA, I<sub>B</sub><sup>1</sup> = I<sub>B</sub><sup>2</sup> = 50 mA.

NOTE: National preferred device for each process in **bold**. Number shown in parentheses indicates location (section-page) of device datasheet.